NSN 5962-01-420-4644

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Body Leng	the
0.358 inche	
Body Widt	
0.358 inche	
Body Heig	
0.100 inche	
	Power Dissipation Rating:
1.0 watts	
	Tempurature Range:
	0 degrees celsius
	empurature Range:
	0 degrees celsius
End Applie	•
Pacer daw	
Features F	rovided:
Burn in and	l electrostatic sensitive and hermetically sealed and programmed and positive outputs and monolithic
Inclosure	
Ceramic ar	d glass
	Configuration:
Leadless fl	at pack
Output Log	gic Form:
Transistor-	ransistor logic
Input Circo	uit Pattern:
14 input	
Criticality	Code Justification:
Cbbl	
Case Outli	ne Source And Designator:
C-2 mil-m-3	38510
Terminal S	Surface Treatment:
Solder	
Product N	ame:
Microcircui	, programmed (pal 16r4a)
Voltage Ra	ting And Type Per Characteristic:
7.0 volts p	ower source
Time Ratir	g Per Chacteristic:
30.00 nanc	seconds propagation delay time, high to low level output and 30.00 nanoseconds propagation delay time, low to high level
output	
Memory D	evice Type:
Pal	
Special Fe	
Altered iter	n, made from device p/n 81036102x, cage 67268, microcircuit, memory, programmable logic, monolithic silicon

Test Data Document:

96906-mil-std883 standard (includes industry or association standards, individual manufactureer standards, etc.).

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Terminal Type And Quantity:

20 leadless

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

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